

RGWS60TS65D

650V 30A Field Stop Trench IGBT

V _{CES}	650V
I _{C (100°C)}	30A
V _{CE(sat) (Typ.)}	1.6V
P_D	156W

● Outline TO-247GE (1) (2)(3)

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating; RoHS Compliant

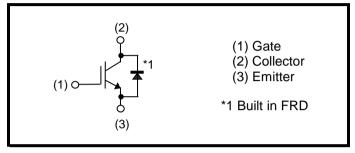
Application

PFC

Solar converters

Mid to high switching frequency converters

●Inner Circuit



Packaging Specifications

	Packaging	Tube
	- ackaging	Tube
	Reel Size (mm)	-
Туре	Tape Width (mm)	-
	Basic Ordering Unit (pcs)	600
	Packing Code	C13
	Marking	RGWS60TS65D

● **Absolute Maximum Ratings** (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	51	А
Collector Current	T _C = 100°C	I _C	32	А
Pulsed Collector Current		I _{CP} *1	90	А
Diode Forward Current	T _C = 25°C	I _F	23	А
	T _C = 100°C	I _F	13	А
Diode Pulsed Forward Current		I _{FP} *1	60	А
Power Dissipation	T _C = 25°C	P _D	156	W
Power Dissipation	T _C = 100°C	P _D	78	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiailletei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.96	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	2.88	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Doromotor	Symbol	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V$, $V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 13.3mA$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = 30A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.6 2.0	2.0	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
Input Capacitance	C _{ies}	$V_{CE} = 30V$,	-	1680	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$,	-	47	-	pF
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	31	-	
Total Gate Charge	Q_g	V _{CE} = 400V,	-	58	-	_
Gate - Emitter Charge	Q_ge	$I_{\rm C} = 30A$,	-	12	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	24	-	
Turn - on Delay Time	t _{d(on)}		-	32	-	_
Rise Time	t _r	$I_C = 30A, V_{CC} = 400V,$	-	12	-	ns mJ
Turn - off Delay Time	t _{d(off)}	$V_{GE} = 15V, R_G = 10\Omega,$ $T_j = 25^{\circ}C$ Inductive Load * E_{on} include diode reverse recovery	-	91	-	
Fall Time	t _f		-	46	-	
Turn - on Switching Loss	E _{on}		-	0.50	-	
Turn - off Switching Loss	E _{off}	·	-	0.45	-	
Turn - on Delay Time	t _{d(on)}		-	31	-	
Rise Time	t _r	$I_C = 30A, V_{CC} = 400V,$ $V_{GF} = 15V, R_G = 10\Omega,$	-	13	-	no
Turn - off Delay Time	t _{d(off)}	$T_i = 175^{\circ}C$	-	101	-	ns
Fall Time	t _f	Inductive Load	-	74	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	0.51	-	m l
Turn - off Switching Loss	E _{off}		-	0.56	-	mJ
Reverse Bias Safe Operating Area	RBSOA	$I_C = 90A$, $V_{CC} = 520V$ $V_P = 650V$, $V_{GE} = 15V$ $R_G = 100\Omega$, $T_j = 175^{\circ}C$	FU	LL SQUA	RE	-

●FRD Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
		I _F = 10A,				
Diode Forward Voltage	V_{F}	$T_j = 25^{\circ}C$	-	1.45	1.9	V
		T _j = 175°C	-	1.4	-	
Diode Reverse Recovery Time	t _{rr}		-	88	-	ns
Diode Peak Reverse Recovery Current	I _{rr}	$I_F = 10A,$ $V_{CC} = 400V,$ $di_F/dt = 200A/\mu s,$ $T_j = 25^{\circ}C$	-	5.9	-	А
Diode Reverse Recovery Charge	Q _{rr}		-	0.28	-	μC
Diode Reverse Recovery Energy	Err		-	17.6	-	μJ
Diode Reverse Recovery Time	t _{rr}	$I_F = 10A$, $V_{CC} = 400V$, $di_F/dt = 200A/\mu s$, $T_j = 175^{\circ}C$	-	105	-	ns
Diode Peak Reverse Recovery Current	I _{rr}		-	6.9	-	А
Diode Reverse Recovery Charge	Q _{rr}		-	0.42	-	μC
Diode Reverse Recovery Energy	Err		-	28.8	-	μJ

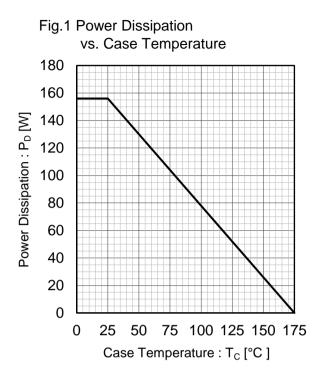


Fig.2 Collector Current vs. Case Temperature 60 50 Collector Current : Ic [A] 40 30 20 10 ≤ 175°C _{GE} ≥ 15V 0 50 75 100 125 150 175 25 0 Case Temperature : T_C [°C]

Fig.3 Forward Bias Safe Operating Area

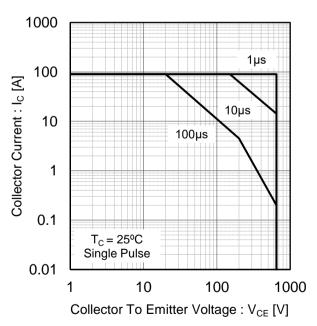


Fig.4 Reverse Bias Safe Operating Area

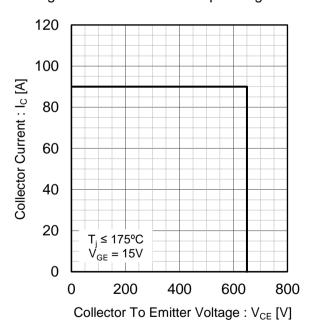


Fig.5 Typical Output Characteristics

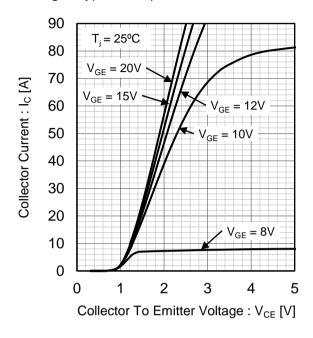


Fig.6 Typical Output Characteristics

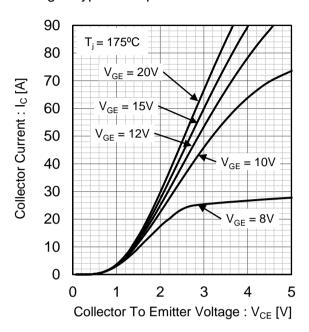


Fig.7 Typical Transfer Characteristics

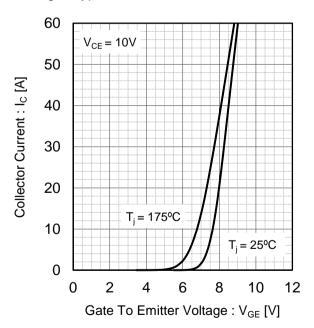
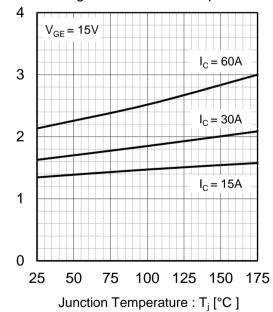


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



Collector To Emitter Saturation

Voltage: V_{CE(sat)} [V]

Fig.9 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

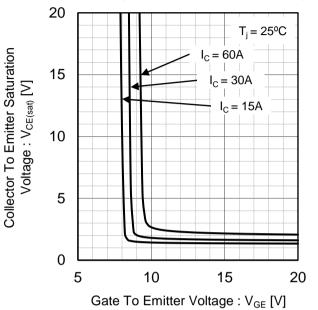


Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

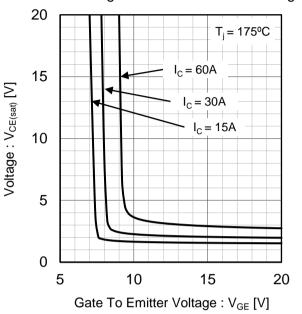


Fig.11 Typical Switching Time vs. Collector Current

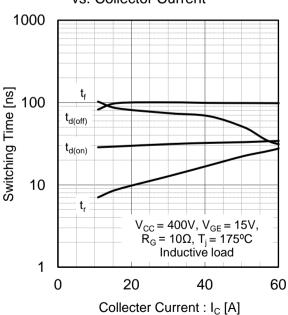
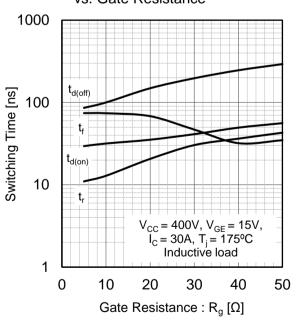


Fig.12 Typical Switching Time vs. Gate Resistance



Collector To Emitter Saturation

0.1

0.01

0

 E_{on}

Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 E_{off}

20

 V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10 Ω , T_{j} = 175°C Inductive load

40

Collecter Current : I_C [A]

60

vs. Gate Resistance 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ Eon 0.1 V_{CC} = 400V, I_{C} = 30A, V_{GE} = 15V, T_{j} = 175°C Inductive load 0.01 20 0 10 30 40 50

Gate Resistance : $R_G[\Omega]$

Fig.14 Typocal Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector to Emitter Voltage 10000 \mathbf{C}_{ies} 1000 Capacitance [pF] 100 10 $\mathsf{C}_{\mathsf{res}}$ f = 1MHz $V_{GE} = 0V$ $T_i = 25^{\circ}C$ 1 0.01 0.1 1 10 100 Collector To Emitter Voltage: V_{CE} [V]

Fig.16 Typical Gate Charge 15 Gate To Emitter Voltage: VGE [V] 10 5 $V_{CC} = 400V$ $\tilde{l}_{C} = 30A$ $T_i = 25^{\circ}C$ 0 0 20 40 60 Gate Charge: Qq [nC]

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Fig.17 Typical Diode Forward Current vs. Forward Voltage 60 50 Forward Current : I_F [A] 40 $T_i = 25^{\circ}C$ 30 $T_i = 175^{\circ}C$ 20 10 0 2 3 0 1 4 5 Forward Voltage: V_F [V]

Vs. Forward Current

200 $T_{i} = 175^{\circ}C$ $T_{i} = 25^{\circ}C$ $T_{i} = 25^{\circ}C$ $T_{i} = 200$ $T_{i} = 200$

Forward Current : I_F [A]

Fig.18 Typical Diode Revese Recovery Time

Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current 15 Reverse Recovery Current : Irr [A] $T_i = 175^{\circ}C$ 10 $T_i = 25^{\circ}C$ 5 $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ Inductive load 0 5 10 15 20 Forward Current : I_F [A]

Charge vs. Forward Current 1 Reverse Recovery Charge : Qr [µC] 0.8 0.6 $T_i = 175^{\circ}C$ 0.4 0.2 $T_i = 25^{\circ}C$ $V_{CC} = 400V$ di_F/dt = 200A/µs Inductive load 0 5 10 15 20 Forward Current : I_F [A]

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Fig.20 Typical Diode Rrverse Recovery

Fig.21 Typical IGBT Transient Thermal Impedance

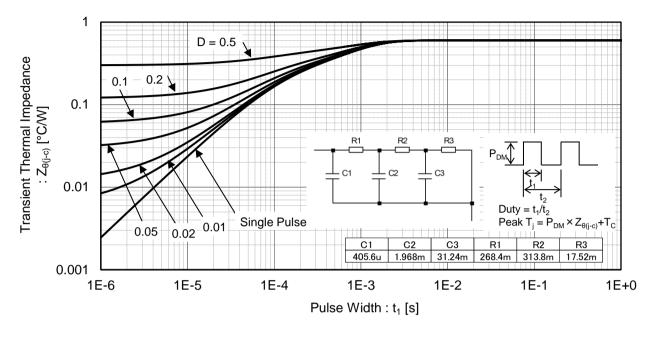
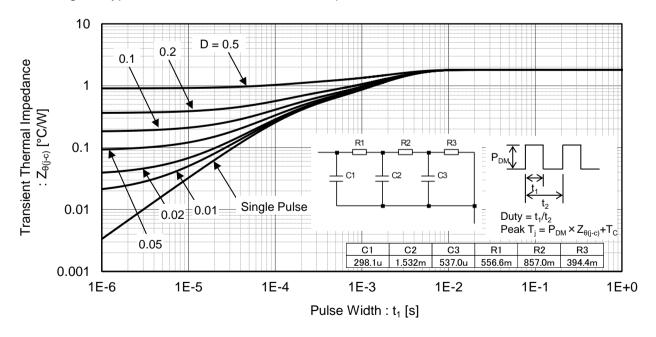


Fig.22 Typical Diode Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

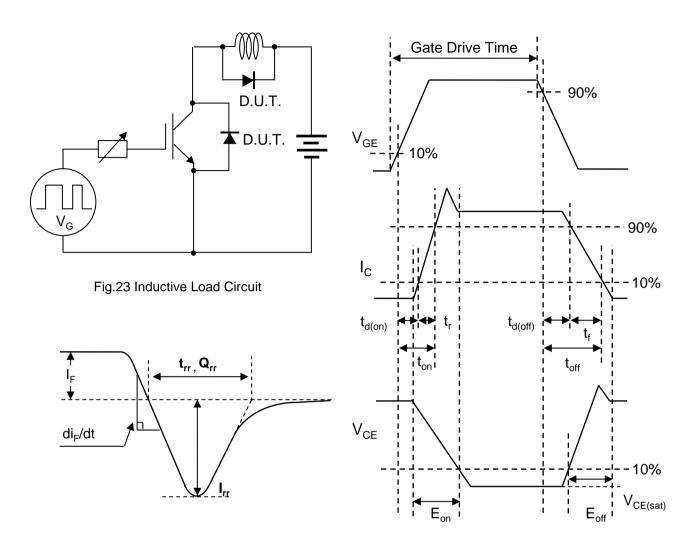


Fig.25 Diode Reverse Recovery Waveform

Fig.24 Inductive Load Waveform

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